

BC847BS

45 V, 100 mA NPN/NPN general-purpose transistor Rev. 03 — 18 February 2009 Produ

Product data sheet

1. Product profile

1.1 General description

NPN/NPN general-purpose transistor pair in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

PNP/PNP complement: BC857BS.

1.2 Features

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and board space
- No mutual interference between the transistors

1.3 Applications

■ General-purpose switching and amplification

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V_{CEO}	collector-emitter voltage	open base	-	-	45	V
I _C	collector current		-	-	100	mA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$	200	-	450	



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2. Pinning information

Table 2. Pinning

Table 2.	Filling		
Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1	D. D. D.	0 5 4
2	base TR1		6 5 4
3	collector TR2		TR2
4	emitter TR2	0	(TR1)
5	base TR2	□1 □2 □3	
6	collector TR1		1 2 3
			sym020

3. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
BC847BS	SC-88	plastic surface-mounted package; 6 leads	SOT363			

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
BC847BS	1F*

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

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5. Limiting values

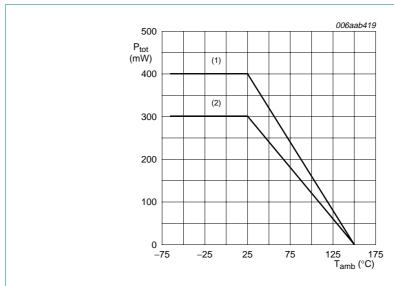
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	45	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current		-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1] -	220	mW
			[2] _	250	mW
Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	300	mW
			[2] _	400	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².



- (1) FR4 PCB, mounting pad for collector 1 cm²
- (2) FR4 PCB, standard footprint

Fig 1. Per device: Power derating curves SOT363 (SC-88)

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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	or					
· · (II(J-a)	thermal resistance from junction to ambient	in free air	[1]	-	568	K/W
		<u></u>	[2]	-	500	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	230	K/W
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	416	K/W
			[2] _	-	313	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

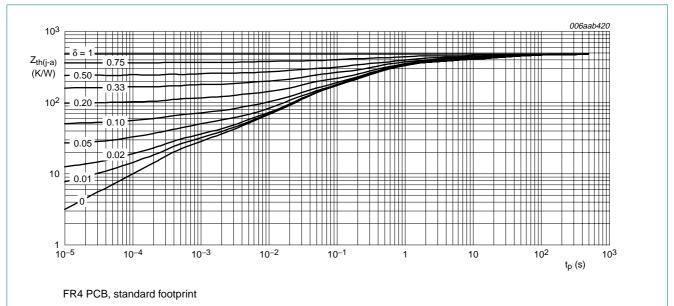
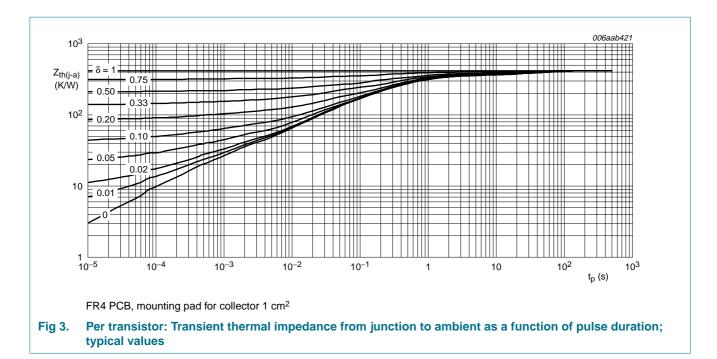


Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

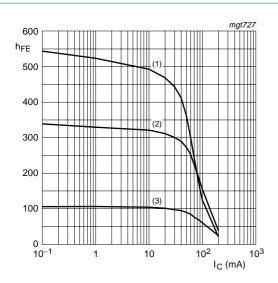
Table 7. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	Per transistor					
I _{CBO}	collector-base cut-off	$V_{CB} = 30 \text{ V}; I_{E} = 0 \text{ A}$	-	-	15	nA
	current	$V_{CB} = 30 \text{ V; } I_{E} = 0 \text{ A;}$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$	200	-	450	
V_{CEsat}	collector-emitter	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	100	mV
	saturation voltage	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$	[1] -	-	300	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	755	-	mV
V_{BE}	base-emitter voltage	$I_C = 2 \text{ mA}$; $V_{CE} = 5 \text{ V}$	580	655	700	mV
C _c	collector capacitance	$I_E = i_e = 0 A; V_{CB} = 10 V;$ f = 1 MHz	-	-	1.5	pF
C _e	emitter capacitance	$I_C = I_c = 0 \text{ A}; V_{EB} = 0.5 \text{ V};$ f = 1 MHz	-	11	-	pF
f _T	transition frequency	$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V};$ f = 100 MHz	100	-	-	MHz

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$.

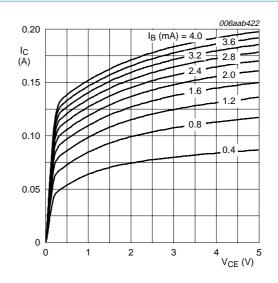
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$$V_{CE} = 5 V$$

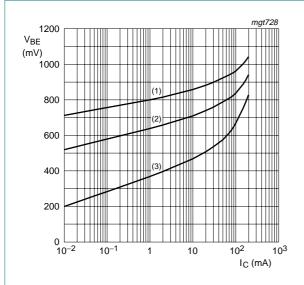
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \,^{\circ}C$

Fig 4. Per transistor: DC current gain as a function of collector current; typical values



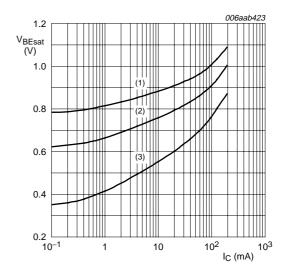
 $T_{amb} = 25 \, ^{\circ}C$

Fig 5. Per transistor: Collector current as a function of collector-emitter voltage; typical values



- $V_{CE} = 5 V$
- (1) $T_{amb} = -55 \,^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 150 \, ^{\circ}C$

Fig 6. Per transistor: Base-emitter voltage as a function of collector current; typical values

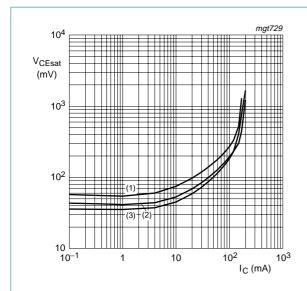


 $I_{\rm C}/I_{\rm B} = 20$

- (1) $T_{amb} = -55$ °C
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 150 \, ^{\circ}C$

Fig 7. Per transistor: Base-emitter saturation voltage as a function of collector current; typical values

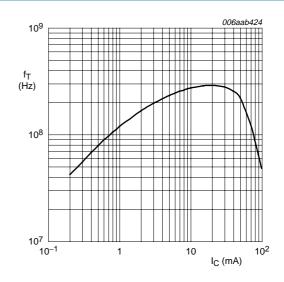
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 $I_{\rm C}/I_{\rm B} = 20$

- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 8. Per transistor: Collector-emitter saturation voltage as a function of collector current; typical values

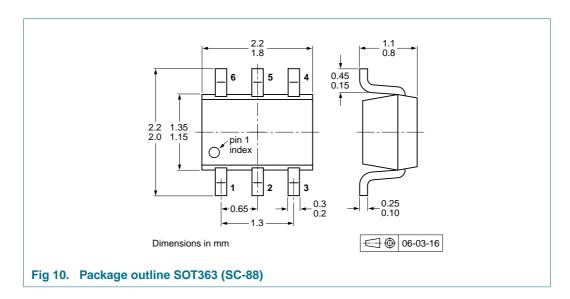


 V_{CE} = 5 V; f = 1 MHz; T_{amb} = 25 °C

Fig 9. Per transistor: Transition frequency as a function of collector current; typical values

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8. Package outline



9. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing quantity	
				3000	10000
BC847BS	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-165

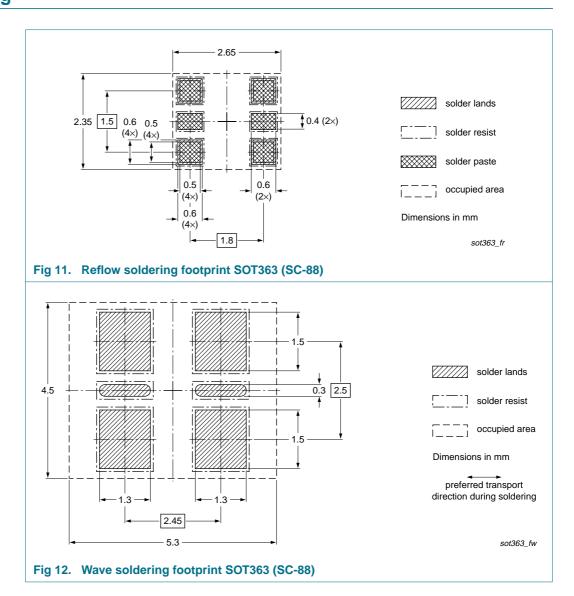
^[1] For further information and the availability of packing methods, see Section 13.

[2] T1: normal taping

[3] T2: reverse taping

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10. Soldering



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11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BC847BS_3	20090218	Product data sheet	-	BC847BS_2		
Modifications:	 The format of NXP. 	f this data sheet has been r	edesigned to comply wit	th the new identity guidelines		
	 Legal texts h 	nave been adapted to the ne	ew company name whe	re appropriate.		
	Section 4 "Marking": updated					
	Section 7 "Characteristics": enhanced					
	 Section 9 "Packing information": added 					
	Section 10 "	Soldering": added				
	Section 12 "	Legal information": updated				
BC847BS_2	19990428	Product specification	-	BC847BS_1		
BC847BS_1	19970714	Product specification	-	-		

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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